

P-Ch MOSFET

General Description

The WSK92P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSK92P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

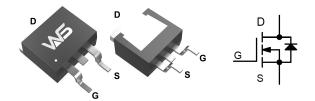
Product Summery

BVDSS	RDSON ID		
-60V	10mΩ	-90A	

Applications

- Power Management
- Load Switch

TO-263-2L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-60	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, -V _{GS} @ -10V	-90	Α	
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V	-40	А	
I _{DM}	Pulsed Drain Current	-190	А	
P _D @T _C =25°C	Total Power Dissipation	96	W	
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$	
TJ	Operating Junction Temperature Range -55 to 150		${\mathbb C}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case		1.3	°C/W



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P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
В	Statia Drain Source On Begintance	V _{GS} =-10V , I _D =-18A		10	14	m()
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-12A		13	18	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250uA$	-1.1	-1.8	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-48V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, V_{DS} =0V			±100	nA
Qg	Total Gate Charge	Vpc 20 V Vcc 40 V		89		
Q_{gs}	Gate-Source Charge	VDS = -30 V, VGS = -10 V, ID = -17A		12		nC
Q_gd	Gate-Drain Charge			32		
T _{d(on)}	Turn-On Delay Time	VDD = -30 V,		15		
Tr	Rise Time	$RL = 30\Omega$, $ID = -1$ A,		13		no
$T_{d(off)}$	Turn-Off Delay Time	$V_{GEN} = -10 \text{ V}, R_g = 6\Omega$		110		ns
T _f	Fall Time			60		
C _{iss}	Input Capacitance	V _{DS} =-30V,V _{GS} =0V, f=1.0MHz		4066		
Coss	Output Capacitance			501		pF
C _{rss}	Reverse Transfer Capacitance			291		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T _C =25 °C			-40	Α
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

A: The value of ReJA is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



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P-Channel Typical Characteristics

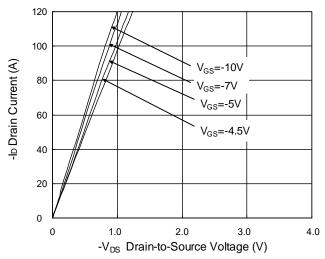


Fig.1 Typical Output Characteristics

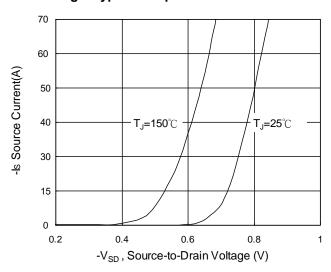


Fig.3 Source Drain Forward Characteristics

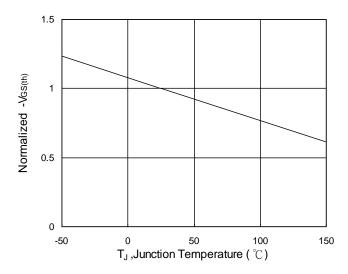


Fig.5 Normalized $V_{\text{GS(th)}}$ vs T_{J}

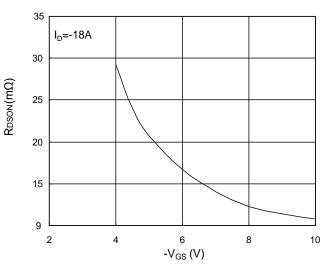


Fig.2 On-Resistance vs G-S Voltage

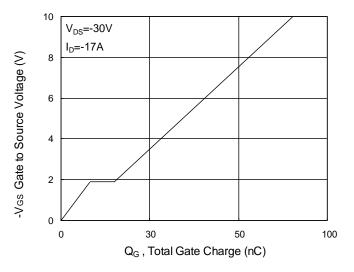


Fig.4 Gate-Charge Characteristics

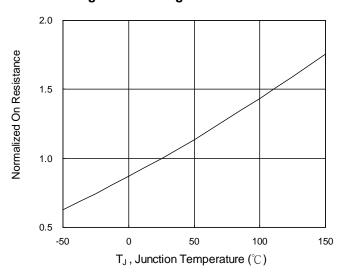


Fig.6 Normalized R_{DSON} vs T_J





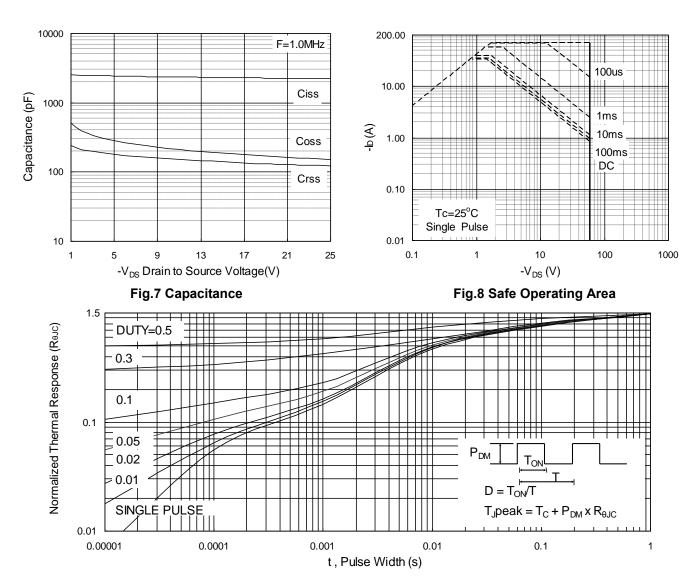


Fig.9 Normalized Maximum Transient Thermal Impedance

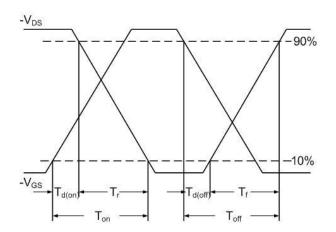


Fig.10 Switching Time Waveform

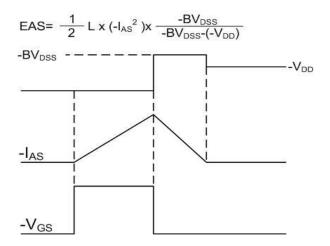


Fig.11 Unclamped Inductive Waveform



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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